CLAIMS

What is claimed is:

BUR9-2001-0012-US1

1		1.	A method of performing model to hardware correlation, comprising:
2			simulating models based upon design criteria;
3			manufacturing devices based upon said design criteria;
4			evaluating features of said devices during said manufacturing to produce in-line test
5		param	etric data;
6	122		comparing said models to said in-line test parametric data to obtain correlation data; and
7	They of The Court and they they they they they they they they		modifying said simulating according to said correlation data.
1	Jung of Jun B	2.	The method in claim 1, wherein said simulating produces geometric, DC, AC, and delay
2		stage s	simulated parameters, and
3	Hard Broke Mann Long H. H.		wherein said in-line test parametric data includes geometric, DC, AC, and delay stage test
4		parame	eters.
1		3.	The method in claim 1, wherein said modifying produces a modified simulation and said
2		method	d further comprises identifying, in a characterization map, ones of said devices that match
3		models	s produced by said modified simulation.
1		4.	The method in claim 1, wherein:
2			said devices comprise semiconductor devices;

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3	•	said models include modeled threshold voltage values;
4		said in-line test parametric data includes test threshold voltage values;
5		said comparing compares said modeled threshold voltage values and said test threshold
6	voltag	ge values to produce a threshold voltage adder; and
7		said modifying includes adding said threshold voltage adder to said modeled threshold
8	voltag	ge values.
1	5.	The method in claim 1, wherein:
2	- 120g	said devices comprise semiconductor devices;
3	The second secon	said models include modeled saturated current values;
4	Here is a second	said in-line test parametric data includes test saturated current values;
3 4 5 6 1		said comparing compares said modeled saturated current values and said test saturation
6	satura	ted current values to produce a saturated current error value.
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1	<u> </u>	The method in claim 1, wherein:
2		said devices comprise semiconductor devices;
3		said models include modeled delay per stage values;
4		said in-line test parametric data includes test delay per stage values;
5		said comparing compares said modeled delay per stage values and said test saturation

delay per stage values to produce a delay per stage error value.

- 7. The method in claim 1, further comprising culling said in-line test parametric data to retain selected geometric, D.C., A.C. and delay test parameters.
- 8. The method in claim 1, further comprising identifying defective devices and removing said defective devices from said in-line test parametric data.
- 9. A method of correcting a hardware modeling process, said method comprising:
 manufacturing devices based on design criteria;
 measuring features of said devices to produce measured features;
 isolating a portion of said modeling process;

supplying at least one of said measured features to said portion of said modeling process, wherein said portion of said modeling process outputs a simulated result;

comparing said simulated result to a corresponding measured feature of said measured features; and calculating a correction to said portion of said modeling process based on said comparing.

- 10. The method in claim 9, wherein said simulated result and said corresponding measured
- 1 11. The method in claim 9, wherein said portion of said modeling process simulates an
 integrated circuit design to model one of saturation threshold voltage, saturated source/drain
 current, and delay per stage.

feature comprise one of a voltage, current, and physical dimension.

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- 1 12. The method in claim 9, further comprising repeating said method for second portions of said modeling process to produce second corrections.
- 1 13. The method in claim 12, further comprising modifying said modeling process based on said correction and said second corrections, such that said modeling process automatically makes said corrections after performing a simulation.
- 1 14. The method in claim 9, wherein said measuring comprises measuring physical

 2 15 dimensions and performance operations of said devices at different points of said manufacturing

 3 15 of said devices.
 - 15. The method in claim 9, further comprising performing a statistical analysis based on results of said comparing process.
 - 16. A method of performing model to hardware correlation for semiconductor chips, comprising:
 - obtaining fabrication in-line parametric data;
- 4 extracting first parameters from said parametric data to make a first set of go-data:
 - calculating a first simulated threshold voltage saturation and first simulated saturated source/drain current based on said first set of go-data using a modeling program;

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performing a first comparing of said first simulated threshold voltage saturation to an inline parametric threshold voltage saturation from said parametric data and a first comparing of said first simulated saturated source/drain current to an in-line parametric saturated source/drain current from said parametric data;

calculating a threshold voltage adder from said first comparing; and correcting said modeling program using said threshold voltage adder.

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17. The method in claim 16, further comprising

adding said threshold voltage adder to said first set of go-data to make a second set of go-data;

calculating a second simulated threshold voltage saturation and second simulated saturated source/drain current based on said second set of go-data using said modeling program; performing a second comparing of said second simulated threshold voltage saturation to said in-line parametric threshold voltage saturation and a second comparing of said second simulated saturated source/drain current;

verifying that said threshold voltage adder corrected said second simulated threshold voltage saturation and said second simulated saturated source/drain current.

18. The method in claim 17, further comprising calculating a percentage error based on said second comparing process and adding said percentage error to said second set of go-data to make a third set of go-data.

1		19.	The method in claim 18, further comprising:	
2			calculating a simulated delay-per-stage based on said third set of go-data using said	
3		model	ing program;	
4			performing a third comparing of said simulated delay-per-stage to an in-line parametric	
5		delay-	per-stage from said parametric data; and	
6			calculating a delay-per-stage error based on said third comparing process.	
1	g mag	20.	The method in claim 19, further comprising:	
2			adding said delay-per-stage error to said third set of go-data to make a final set of go-	
3	Thur The	data; a	nd	
4	an an an an		outputting statistics based on said threshold voltage adder, said percentage error and said	
5	and the great time for the state is carry as one carry as the state of	delay-	per-stage error.	
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1		21.	The method in claim 18, further comprising:	
2			performing a fourth comparing of parametric yield data from said final set of go-data to	
3		functional yield data from wafer final test servers;		
4			selecting acceptable chips which have good parametric yield data and good functional	
5		yield d	ata from said fourth comparing process; and	

creating a model to hardware wafer map showing locations of said acceptable chips.

1	22.	The method in claim 21, further comprising performing a model to hardware comparison
2	using s	said model to hardware wafer map.

- 23. The method in claim 16, further comprising, after said extracting, removing defective chips from said first parameters to make said first set of go-data.
- 24. A method of performing model to hardware correlation for semiconductor chips, comprising:
 - obtaining fabrication in-line parametric data;
 extracting first parameters from said parametric data to make a first set of go-data;
 calculating a first simulated threshold voltage saturation and first simulated saturated
 source/drain current based on said first set of go-data using a modeling program;
 - performing a first comparing of said first simulated threshold voltage saturation to an inline parametric threshold voltage saturation from said parametric data and a first comparing of said first simulated saturated source/drain current to an in-line parametric saturated source/drain current from said parametric data;
 - calculating a threshold voltage adder from said first comparing;
 - adding said threshold voltage adder to said first set of go-data to make a second set of go-data;
 - calculating a second simulated threshold voltage saturation and second simulated saturated source/drain current based on said second set of go-data using said modeling program;

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performing a second comparing of said second simulated threshold voltage saturation to
said in-line parametric threshold voltage saturation and a second comparing of said second
simulated saturated source/drain current to said in-line parametric saturated source/drain current;
calculating a percentage error based on said second comparing process and adding said
percentage error to said second set of go-data to make a third set of go-data:

calculating a simulated delay-per-stage based on said third set of go-data using said modeling program;

performing a third comparing of said simulated delay-per-stage to an in-line parametric delay-per-stage from said parametric data;

calculating a delay-per-stage error based on said third comparing process;

adding said delay-per-stage error to said third set of go-data to make a final set of go-data; and

correcting said modeling program using said final set of go-data.

- 25. The method in claim 24, further comprising, after said extracting, removing defective chips from said first parameters to make said first set of go-data.
- 26. The method in claim 24, further comprising, after said second comparing, verifying that said threshold voltage adder corrected said second simulated threshold voltage saturation and said second simulated saturated source/drain current.

1	27.	The method in claim 24, further comprising outputting statistics based on said threshold
2	voltage	e adder, said percentage error and said delay-per-stage error.
1	28.	The method in claim 24, further comprising:
2		performing a fourth comparing of parametric yield data from said final set of go-data to
3	function	onal yield data from wafer final test servers;
4		selecting acceptable chips which have good parametric yield data and good functional
5	yield d	ata from said fourth comparing process;
6		creating a model to hardware wafer map showing locations of said acceptable chips; and
7		performing a model to hardware comparison using said model to hardware wafer map.
7 1 2 3 4 5 4 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	29.	A method of performing model to hardware correlation for semiconductor chips,
2	compr	ising:
3		obtaining fabrication line parametric data;
4		extracting first parameters from said parametric data;
5	•	removing defective chips from said first parameters to make a first set of go-data;
6		calculating a first simulated threshold voltage saturation and first simulated saturated
7	source	/drain current based on said first set of go-data using a modeling program;
8		performing a first comparing of said first simulated threshold voltage saturation to an in
9	line pa	arametric threshold voltage saturation from said parametric data and a first comparing of
10	said fi	rst simulated saturated source/drain current to an in-line parametric saturated source/drain

current from said parametric data;

12	calculating a threshold voltage adder from said first comparing;
13	adding said threshold voltage adder to said first set of go-data to make a second set of go-
14	data;
15	calculating a second simulated threshold voltage saturation and second simulated
16	saturated source/drain current based on said second set of go-data using said modeling program;
17	performing a second comparing of said second simulated threshold voltage saturation to
18	said in-line parametric threshold voltage saturation and a second comparing of said second
19	simulated saturated source/drain current to said in-line parametric saturated source/drain current;
20	verifying that said threshold voltage adder corrected said second simulated threshold
21 0 0 22 23 23	voltage saturation and said second simulated saturated source/drain current;
22	calculating a percentage error based on said second comparing process and adding said
23	percentage error to said second set of go-data to make a third set of go-data;
24 :	calculating a simulated delay-per-stage based on said third set of go-data using said
25 26 26 27	modeling program;
26	performing a third comparing of said simulated delay-per-stage to an in-line parametric
27	delay-per-stage from said parametric data;
28	calculating a delay-per-stage error based on said third comparing process;
29	adding said delay-per-stage error to said third set of go-data to make a final set of go-
30	data;
31	outputting statistics based on said threshold voltage adder, said percentage error and said
32	delay-per-stage error;

33	performing a fourth comparing of parametric yield data from said final set of go-data to	
34	functional yield data from wafer final test servers;	
35	selecting acceptable chips which have good parametric yield data and good functional	
36	yield data from said fourth comparing process;	
37	creating a model to hardware wafer map showing locations of said acceptable chips; and	
38	performing a model to hardware comparison using said model to hardware wafer map.	
1	30. A program storage device readable by machine, tangibly embodying a program of	
2	instructions executable by the machine to perform method steps for performing model to	
3 4 7 7 7 7 6 6	hardware correlation, comprising:	
4	simulating models based upon design criteria;	
5	manufacturing devices based upon said design criteria;	
6	evaluating features of said devices during said manufacturing to produce in-line test	
7 III	parametric data;	
7 8 m	comparing said models to said in-line test parametric data to obtain correlation data; and	
9	modifying said simulating according to said correlation data.	
1	31. The program storage device as claimed in claim 30, wherein said simulating produces	
2	geometric, DC, AC, and delay stage simulated parameters, and	
3	wherein said in-line test parametric data includes geometric, DC, AC, and delay stage test	
4	parameters.	

- The program storage device as claimed in claim 30, wherein said modifying produces a 1 32. modified simulation and said method further comprises identifying, in a characterization map, 2 ones of said devices that match models produced by said modified simulation. 3 The program storage device as claimed method in claim 30, wherein: 1 33. 2 said devices comprise semiconductor devices; 3 said models include modeled threshold voltage values; said in-line test parametric data includes test threshold voltage values; 4 said comparing compares said modeled threshold voltage values and said test threshold 5 6 I voltage values to produce a threshold voltage adder; and said modifying includes adding said threshold voltage adder to said modeled threshold voltage values. I Harry Street H. H. The program storage device as claimed method in claim 30, wherein: 34. said devices comprise semiconductor devices; 3 said models include modeled saturated current values: said in-line test parametric data includes test saturated current values; 5 said comparing compares said modeled saturated current values and said test saturation 6 saturated current values to produce a saturated current error value.
- 1 35. The program storage device as claimed method in claim 30, wherein: 2 said devices comprise semiconductor devices;

- said models include modeled delay per stage values;

 said in-line test parametric data includes test delay per stage values;

 said comparing compares said modeled delay per stage values and said test saturation

 delay per stage values to produce a delay per stage error value.
- 1 36. The program storage device as claimed method in claim 30, further comprising culling said in-line test parametric data to retain selected geometric, D.C., A.C. and delay test parameters.